L Number	Hits	Search Text	DB	Time stamp
1	26	(water with ozone with tank)with(bubbl$3 sparg$3 mix$3) and (ambient "room temperature" temperature)	JPO; DERWENT	2004/06/16 15:08
2	60	(((water with ozone same(bubbl$3 sparg$3 mix$3)) same (wafer semiconductor substrate))) and (temperature C celsius ambient)	JPO; DERWENT	2004/06/16 15:06
3	57	((((water with ozone same(bubbl$3 sparg$3 mix$3)) same (wafer semiconductor substrate))) and (temperature C celsius ambient)) not ((water with ozone with tank)with(bubbl$3 sparg$3 mix$3) and (ambient "room temperature" temperature))	JPO; DERWENT	2004/06/16 15:05
4	15	(((water with ozone same(bubbl$3 sparg$3 mix$3)) same (wafer semiconductor substrate))) and (temperature "°" celsius ambient)	JPO; DERWENT	2004/06/16 15:06
5	0	6649018.pn. and (deg temperature)	JPO; DERWENT	2004/06/16 15:09
6	1	6649018.pn. and (deg temperature)	USPAT	2004/06/16 15:09
7	3	("5464480" | "6080531" | "6187216").PN.	USPAT	2004/06/16 15:09
8	3	(("5464480" | "6080531" | "6187216").PN.) and (deg temperature)	USPAT	2004/06/16 15:10
–	422	134/159	USPAT	2004/01/30 10:43
–	1	6340643.pn.	USPAT	2003/08/07 12:36
–	4	("5405443" | "5599394" | "6059880" | "6245148").PN.	USPAT	2003/08/07 12:37
–	2	("5759918" "5695392").pn.	USPAT	2003/08/14 08:26
–	0	"0776730"	EPO	2003/08/14 08:26
–	0	0776730.ipc.	EPO	2003/08/14 08:27
–	0	776730.ipc.	EPO	2003/08/14 08:27
–	0	00776730.ipc.	EPO	2003/08/14 08:27
–	0	0776730.ipc.	EPO	2003/08/14 08:28
–	1171	Kubo	EPO	2003/08/14 08:28
–	11	Kubo and retaining	EPO	2003/08/14 08:28
–	2	5957764.pn. 5985039.pn. 0793261.ipc.	USPAT; EPO	2003/08/14 11:41
–	3	5957764.pn. 5985039.pn. "0793261"	USPAT; EPO	2003/08/14 11:42
–	1	"0793261"	USPAT; EPO	2003/08/14 11:43
–	0	ep.0793261.	USPAT; EPO	2003/08/14 11:44
–	1	"00793261"	USPAT; EPO	2003/08/14 11:44
–	0	"00793261"	EPO; DERWENT	2003/08/14 11:45
–	236	156/345.11 156/345.23	USPAT	2003/08/14 13:53
–	2807	134/1.3 134/119 134/120 134/136 134/137 134/138 134/140 134/157	USPAT	2003/08/14 13:54
–	1336	(134/1.3 134/119 134/120 134/136 134/137 134/138 134/140 134/157) and (wafer semiconductor substrate)	USPAT	2003/08/14 13:55
–	877	((134/1.3 134/119 134/120 134/136 134/137 134/138 134/140 134/157) and (wafer semiconductor substrate)) and (flip$4 turn$4 rotat$6)	USPAT	2003/08/14 13:56
–	916	((134/1.3 134/119 134/120 134/136 134/137 134/138 134/140 134/157) and (wafer semiconductor substrate)) and etch$3	USPAT	2003/08/14 13:57
–	423	134/159	USPAT	2004/01/30 10:43
–	162	156/345.11	USPAT; US-PGPUB	2004/02/02 14:32
–	3	6383724.pn. 5464480.pn. 6187216.pn.	USPAT	2004/02/04 11:02
–	2017	156/345.11 156/345.18 438/689 216/83 216/93	USPAT	2004/02/04 11:03
–	50	(156/345.11 156/345.18 438/689 216/83 216/93) and (water same ozone)	USPAT	2004/02/04 11:05
–	1	6649018.pn.	EPO; DERWENT	2004/04/22 10:47
–	8	134/113	EPO; DERWENT	2004/04/22 10:47
–	815	134/113	USPAT	2004/04/22 10:48
–	421	water same ozone same (sparger bubbl$3)	EPO; DERWENT	2004/06/03 15:23

-	1369	water same ozone same (sparger bubbl$3)	USPAT; US-PGPUB	2004/06/03 15:24
-	647	water with ozone with (sparger bubbl$3)	USPAT; US-PGPUB	2004/06/03 15:25
-	26	"5750440"	USPAT	2004/06/04 14:25
-	3472	water and ozone and tank	EPO; JPO; DERWENT	2004/06/16 12:41
-	3407	water and ozone and tank	JPO; DERWENT	2004/06/16 12:41
-	2825	water same ozone same tank	JPO; DERWENT	2004/06/16 12:41
-	2216	water with ozone with tank	JPO; DERWENT	2004/06/16 12:42
-	738	(water with ozone with tank) and (bubbl$3 sparg$3 mix$3)	JPO; DERWENT	2004/06/16 12:42
-	651	water with ozone with tank)same(bubbl$3 sparg$3 mix$3	JPO; DERWENT	2004/06/16 12:52
-	539	water with ozone with tank)with(bubbl$3 sparg$3 mix$3	JPO; DERWENT	2004/06/16 14:57
-	22	(water with ozone with tank)with(bubbl$3 sparg$3 mix$3) and (wafer semiconductor substrate)	JPO; DERWENT	2004/06/16 12:45
-	2391	water with ozone same(bubbl$3 sparg$3 mix$3)	JPO; DERWENT	2004/06/16 12:52
-	99	(water with ozone same(bubbl$3 sparg$3 mix$3)) same (wafer semiconductor substrate)	JPO; DERWENT	2004/06/16 15:04
-	84	((water with ozone same(bubbl$3 sparg$3 mix$3)) same (wafer semiconductor substrate)) not ((water with ozone with tank)with(bubbl$3 sparg$3 mix$3) and (wafer semiconductor substrate))	JPO; DERWENT	2004/06/16 13:58